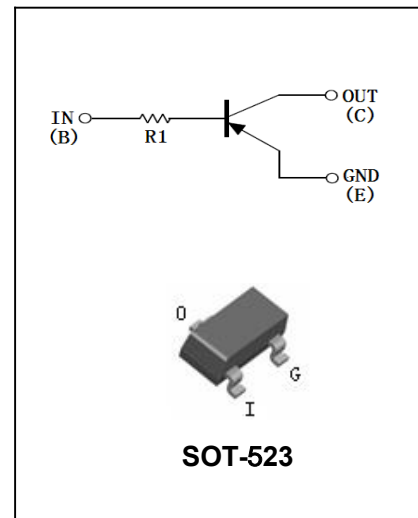


# Digital Transistor

# DTA(R<sub>1</sub>-only SERIES)E

## FEATURES

- Epitaxial planar die construction
- Complementary NPN types available(DTC)
- Built-in biasing resistor, R<sub>1</sub> only
- Also available in lead free version



## APPLICATIONS

- The PNP style digital transistor

## ORDERING INFORMATION

Type No.	Marking	Package Code
DTA114TE	94	SOT-523
DTA143TE	93	SOT-523
DTA144TE	96	SOT-523

## MAXIMUM RATING @ T<sub>A</sub> = 25°C unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C(Max.)</sub>	Collector Current	-100	mA
P <sub>D</sub>	Power Dissipation	150	mW
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient Air *1	306	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction to Case *1	152	°C/W
R <sub>θJL</sub>	Thermal Resistance, Junction to Lead *1	61	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage and Temperature Range	-55 to +150	°C

Note 1: The data tested by surface mounted on a 15mm \* 15mm \* 1mm FR4-epoxy P.C.B



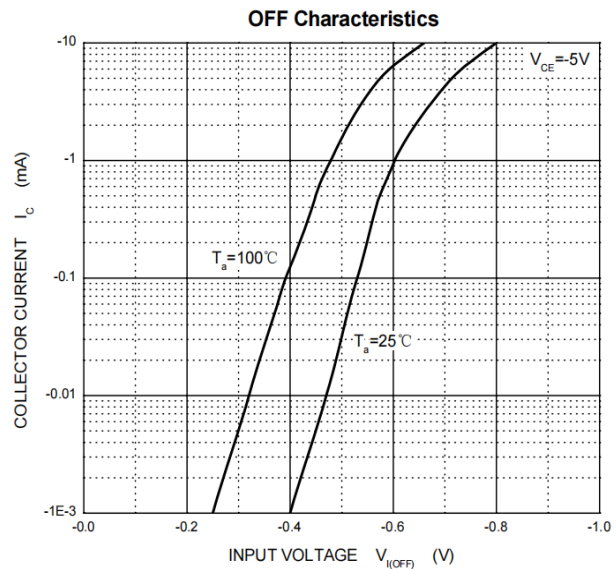
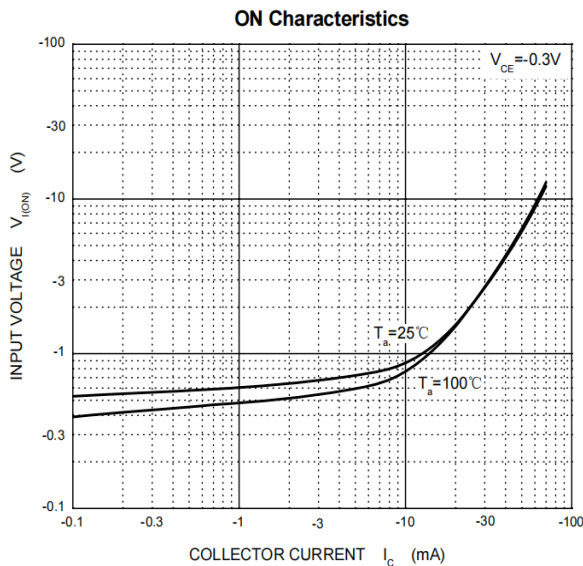
Digital Transistor

DTA(R<sub>1</sub>-only SERIES)E

ELECTRICAL CHARACTERISTICS @ T<sub>A</sub> = 25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =-50μA	-50			V
Collector-Emitter breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =-1mA	-50			V
Emitter-Base breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =-50μA	-5			V
Collector cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V	-	-	-0.5	μA
Emitter cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V	-	-	-0.5	μA
Collector-Emitter saturation voltage DTA114TE DTA143TE DTA144TE	V <sub>CE(sat)</sub>	I <sub>C</sub> /I <sub>B</sub> =-10mA/-1mA I <sub>C</sub> /I <sub>B</sub> =-5mA/-0.25mA I <sub>C</sub> /I <sub>B</sub> =-5mA/-0.5mA			-0.3	V
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> =-1mA, V <sub>CE</sub> =-5V	100	250	600	
Input Resistor(R <sub>1</sub> ) DTA114TE DTA143TE DTA144TE	R <sub>1</sub>		7 3.29 32.9	10 4.7 47	13 6.11 61.1	KΩ
Input Resistor(R <sub>1</sub> )Tolerance	ΔR <sub>1</sub>		-30		+30	%
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>E</sub> =5mA, f=100MHz	-	250	-	MHz

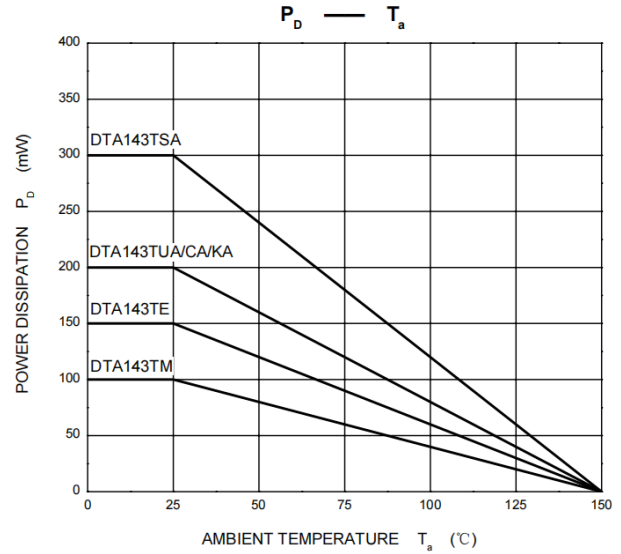
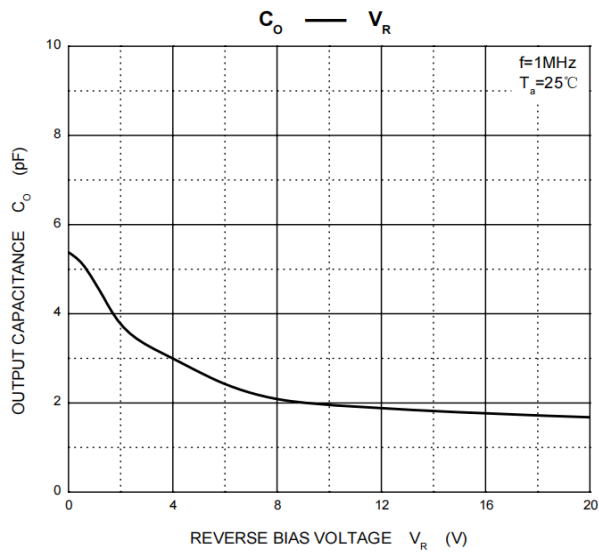
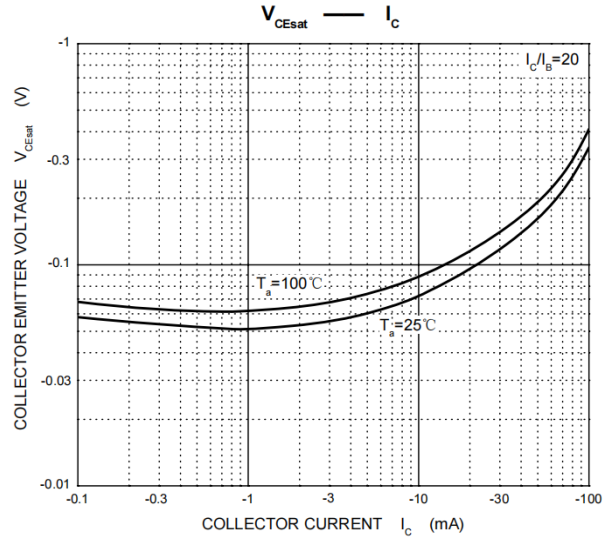
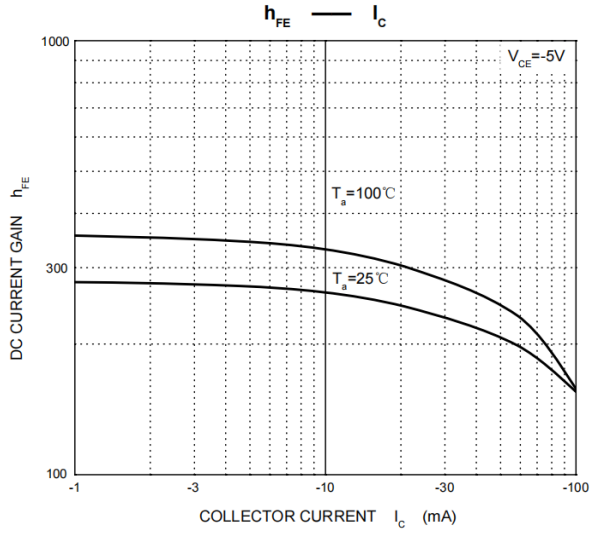
TYPICAL CHARACTERISTICS @ T<sub>a</sub>=25°C unless otherwise specified





# Digital Transistor

# DTA(R<sub>1</sub>-only SERIES)E



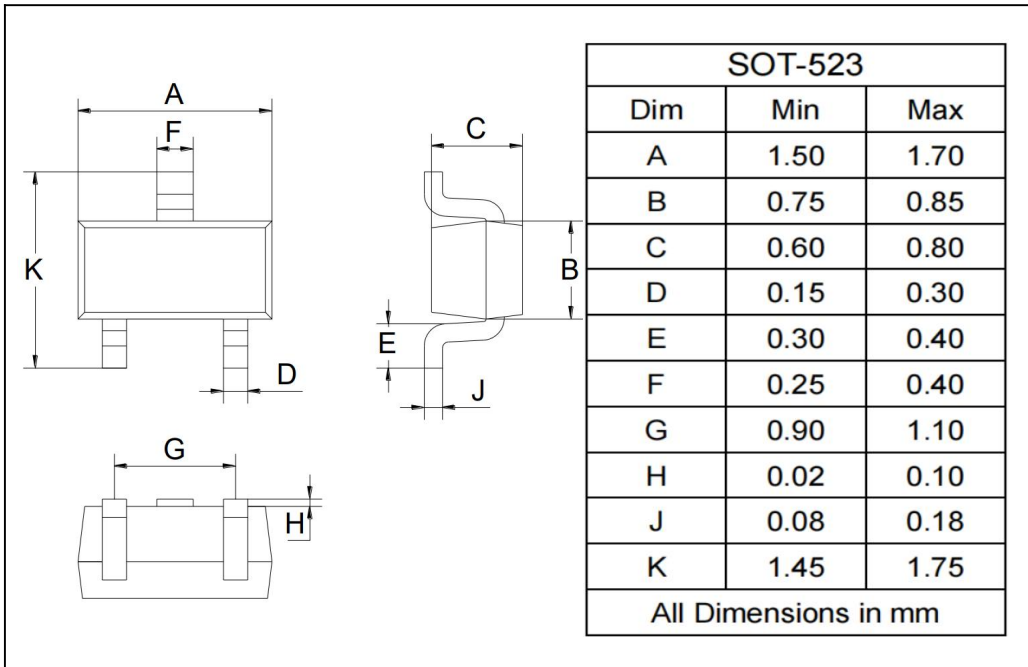
Digital Transistor

DTA(R<sub>1</sub>-only SERIES)E

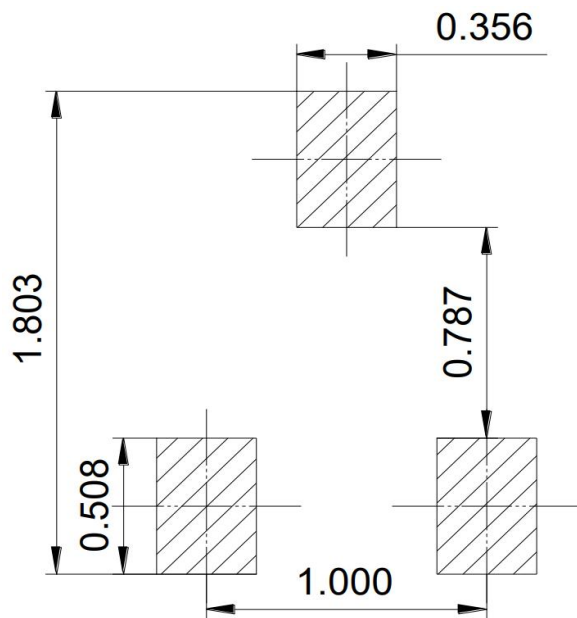
PACKAGE OUTLINE

Plastic surface mounted package

SOT-523



SOLDERING FOOTPRINT



Unit: mm

PACKAGE INFORMATION

Device	Package	Shipping
DTA114TE/143TE/144TE	SOT-523	3000 pcs / Tape & Reel